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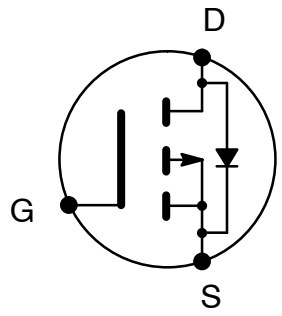
NTE2990
MOSFET
P–Channel, Enhancement Mode
High Speed Switch
TO220 Full Pack

Features:
- Low Drain–Source On–Resistance
- Low Input Capacitance
- High Avalanche Capability Ratings



Applications:
- Switching Regulators
- UPS
- DC–DC Converters
- General Purpose Power Amplifier

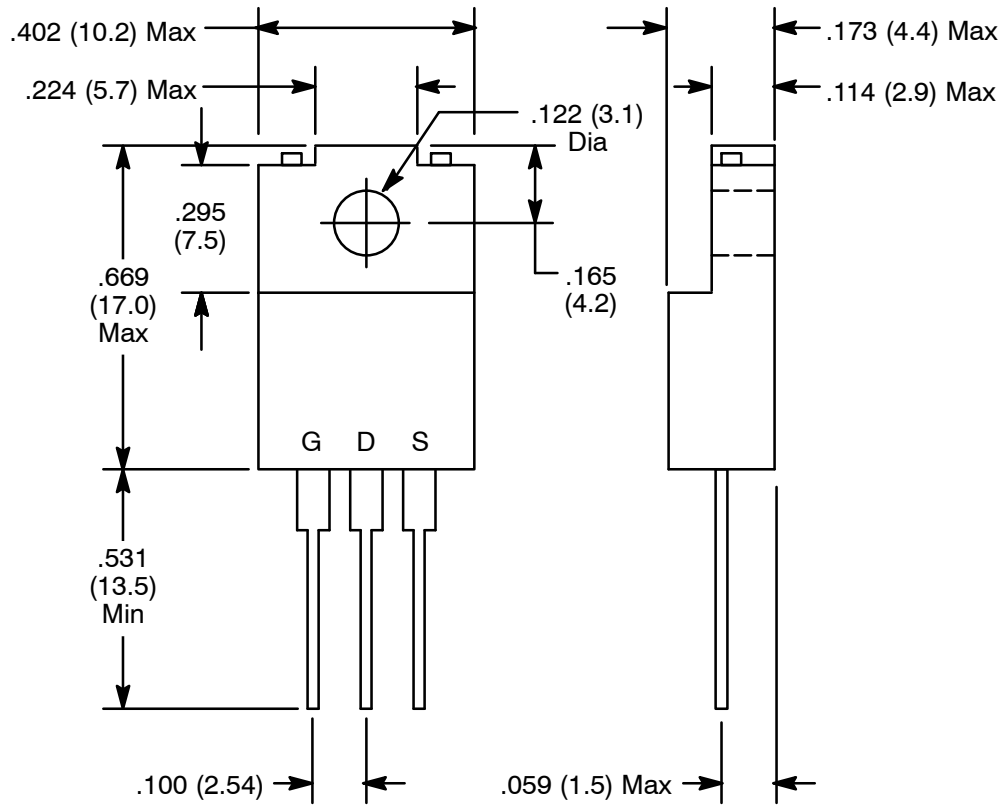
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Drain–Source Voltage, V_{DSS} 250V
Gate–Source Voltage, V_{GSS} . . . . . ±30V
Drain Current, I_D
  Continuous . . . . . ±6A
  Pulsed (Note 1) . . . . . ±24A
Maximum Power Dissipation, P_D
  T_C = +25°C 35W
  T_A = +25°C 2.0W
Single Avalanche Current (Note 2), I_{AS} 6A
Single Avalanche Energy (Note 2), E_{AS} 180mJ
Channel Temperature, T_{ch} . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Thermal Resistance, Junction–to–Ambient, R_{thJA} . . . . . 62.5°C/W
Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 2.77°C/W

Note 1. Pulse Width ≤ 10±s, Duty Cycle ≤ 1%.
Note 2. Starting T_{ch} = +25°C, R_G = 25→, V_{GS} = –20V → 0.

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain−Source On−State Resistance	$R_{DS(on)}$	I_D = 3A, V_{GS} = 10V	–	0.55	0.80	→
Gate Threshold Voltage	$V_{GS(th)}$	I_D = 1mA, V_{DS} = 10V	4.0	4.8	5.5	V
Forward Transfer Admittance	g_{fs}	I_D = 3A, V_{DS} = 10V	2.0	3.5	–	S
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 250V, V_{GS} = 0V	–	–	100	±A
Gate−Source Leakage Current	I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V	–	–	±100	nA
Input Capacitance	C_{iss}	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz	–	1040	–	pF
Output Capacitance	C_{oss}		–	360	–	pF
Reverse Transfer Capacitance	C_{rss}		–	70	–	pF
Turn−On Time	$t_{d(on)}$	V_{DD} = 125V, I_D = 3A, $V_{GS(on)}$ = 10V, R_G = 10→, R_L = 42→	–	25	–	ns
Rise Time	t_r		–	16	–	ns
Turn−Off Time	$t_{d(off)}$		–	47	–	ns
Fall Time	t_f		–	14	–	ns
Total Gate Charge	Q_g	V_{DD} = 200V, V_{GS} = 10V, I_D = 6A	–	23.1	–	nC
Gate−Source Charge	Q_{gs}		–	7.1	–	nC
Gate−Drain (“Miller”) Charge	Q_{gd}		–	12.9	–	nC
Source−Drain Diode Ratings and Characteristics: (T_A = +25°C unless otherwise specified)						
Diode Forward Voltage	V_{DSF}	I_{DR} = 6A, V_{GS} = 0V	–	0.92	–	V
Reverse Recovery Time	t_{rr}	I_{DR} = 6A, V_{GS} = 0V, di/dt = 50A/±s	–	155	–	ns
Reverse Recovered Charge	Q_{rr}		–	930	–	nC



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